# Custom async circuit design from production rules to netlist

Benjamin Hill

benjamin.hill@intel.com

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### Implementing custom circuit designs

#### Our task:

Given a gate-level system expressed as production rule set (PRS), generate netlist (SPICE) and physical implementation (layout)

Do as little full custom design as possible!

Refer to 2022 week 3 sessions describing Yale's open-source automated physical implementation flow



### Production rule basics

### Production rule sets form gates



### Custom design flow



### Simulation options

	Gate level	Switch level	Analog
simulator	prsim, actsim	irsim	Хусе
input	ACT PRS	.sim	SPICE
to generate	write directly or use e.g. chp2prs	prs2sim	prs2net
model	unit delay	RC delay	full analog
fidelity	lowest	medium	highest
speed	fastest	fast	slow

# CMOS transistors





### CMOS transistors



### Transistor operation: cutoff



### Transistor operation: channel formation



### Transistor operation: saturation



### Transistor operation: cutoff





# Layout and sizing





### Design rules

set of geometric restrictions intended to yield high probability of correct fabrication, operation, and lifetime

Table 3 Table 2 - Minimum CDs in Design or on Wafer, required by Technology (Core or Periphery)				
Layer Name	Feature Size	Space Size	Feature Name	Space Name
Field Oxide	0.14	0.27	FOMCD	FOMCDSP
Deep N-Well	3	6.3	DNMCD	DNMCDSP
P-Well Block Mask	0.84	1.27	PWBMCD	PWBMCDSP
P-Well Drain Extended	0.84	1.27	PWDEMCD	PWDEMCDSP
N-Well	0.84	1.27	NWMCD	NWMCDSP
Metal 1	0.14	0.14	MM1CD	MM1CDSP
Metal 1 - Cu	0.14	0.14	MM1_CuCD	MM1_CuCDSP
Via	0.15	0.17	VIMCD	VIMCDSP
Via - Cu	0.18	0.13	VIM_CuCD	VIM_CuCDSP
Capacitor MiM	2	0.84	CAPMCD	CAPMCDSP
Metal 2	0.14	0.14	MM2CD	MM2CDSP
Metal 2 - Cu	0.14	0.14	MM2_CuCD	MM2_CuCDSP
Via 2-TNV	0.28	0.28	VIM2CD	VIM2CDSP
Via 2-S8TM	0.8	0.8	VIM2CD	VIM2CDSP



https://skywater-pdk.readthedocs.io/en/main/rules

### Transistor sizing

# Skywater 130 simplified design rules

λ	75 nm*
L	2λ
$W_N$	6 λ
$W_P$	10 λ

# sky130l prs2net.conf
...
int std\_p\_width 10
int std\_p\_length 2

int std\_n\_width 6
int std\_n\_length 2
...
real p\_n\_ratio 1.512

real weak\_to\_strong\_ratio 0.1

real lambda 7.5e-8



\* minimum feature size for Skywater 130 is 150nm transistor gate length

### Transistor performance scaling intuition

Transistor device with width and length parameters

What happens as we vary them?





### Analogy: resistors



current through resistor (aka "drive strength") is inversely proportional to effective resistance

 $I = \frac{V}{R}$ 



**Increased** resistance, **decreased** current

### Transistor performance scaling intuition



#### **Key performance metric:**

current through transistor effective resistance "drive strength"



### gate Modern transistor architectures drain \_\_\_\_\_ source



Planar

FinFET

Gate-All-Around

### Digital designer summary

Use NMOS in pull-down network, PMOS in pull-up  $\Rightarrow$  single stage logic is always inverting

Transistor drive strength  $\propto \frac{Width}{Length}$  $\Rightarrow$  use minimum gate length for digital logic (usually)

# State-holding gates

### Combinational vs state-holding gates

#### Combinational

• Either UP or DOWN (but not both) is always conducting

#### State-holding

- At times neither UP nor DOWN is conducting
- out is undriven and maintains its previous value

#### Interfering

- Both UP and DOWN conducting simultaneously
- Causes short-circuit/crowbar current through gate, should not be more than transient



### Example state-holding gate: Muller C-element



a & b -> out+ ~a & ~b -> out-



a & b -> \_out- \_out -> out-~a & ~b -> \_out+ ~\_out -> out+



a & b #> \_out-\_out => out-

not CMOS implementable!

inverting C-element plus inverter

shorthand syntax

а	b	out
0	0	0
0	1	hold previous state
1	0	hold previous state
1	1	1

### Problem: undriven dynamic nodes



а	b	_out
0	0	1
0	1	hold previous state
1	0	hold previous state
1	1	0



### C-element PRS to SPICE example

```
defproc celem (bool? a,b; bool! out)
{
    bool _out;
    prs {
        a & b #> _out-
        _out => out-
    }
}
```





		<pre>* act defproc: inv&lt;&gt; * raw ports: in out</pre>
SPICE basics	Define new subcircuit (cell):	
	.subckt name ports	.subckt inv in out
		*.PININFO in:I out:O
		*.POWER VDD Vdd
	Comments begin with $st$	*.POWER GND GND
	Metadata generated by prs2net	*.POWER NSUB GND
		*.POWER PSUB Vdd
		* node flags
		<pre>* out (combinational)</pre>
		* end node flags
	MOSFET instances:	MO_ Vdd in out Vdd p W=1.5U L=0.6U
	M <i>name</i> D G S B type <param=val></param=val>	M1_ GND in out GND n W=0.9U L=0.6U
	End of inv subcircuit:	.ends
		* end of process: inv<>
		* act defproc: buf<>
		* raw ports: in out
		.subckt buf in out
Instan	tiate subcircuits hierarchically:	xstage1 inout inv
	x <i>name</i> ports cellname	<pre>xstage2out out inv</pre>
		.ends
		* end of process: buf<>

### C-element PRS to SPICE example

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ben@summerschool:week3\$

### C-element PRS to SPICE example



### C-element with weak keeper staticizer

```
defproc celem (bool? a,b; bool! out)
{
    bool _out;
    prs {
        a & b #> _out-
        _out => out-
    }
}
```





### Combinational feedback staticizer

Converts state-holding gate to be combinational

**Dual network** = inverse logic function

• Between a network and its dual, exactly one is conducting – never interfering

If neither UP nor DOWN is conducting (original state-holding case), both dual networks will conduct and feedback from out selects which is enabled



### C-element with combinational feedback





### van Berkel C-element

```
defproc celem H (bool? a,b; bool! out)
  bool _out;
  bool nmid[2], pmid[2];
  prs {
    // N-stack
    [keeper=0] a -> nmid[0]-
    [keeper=0] b -> nmid[1]-
    passn (out, nmid[0], nmid[0])
    passn (b, nmid[0], _out)
    passn (a, nmid[1], _out)
    // Symmetric P-stack, out inverter
    ...
```





# Layout generation



### Generating transistor stacks

```
# get_rect.ia: Generate rect layout files for sized cells
# Load design and generate transistor netlist
act:read "sized.act"
act:expand
act:top all cells
ckt:cell-map
ckt:map
ckt:save-sp "all cells.sp"
# Generate layout
load-scm "phydb.scm"
# (area multiplier and aspect ratio arbitrary,
# since we're only creating cells)
phydb:create 2 1 "output.lef"
act:layout:rect
```

> interact -Tsky130l < get\_rect.ia
> mag.pl \*.rect > magic\_cells.tcl
> magic -Tsky130l [source magic\_cells.tcl]

### Auto-generated transistor stacks

### Weak keeper



### **Combinational feedback**



Complete cell wiring for use with place and route flow (e.g. gridded cell or standard cell)

### Gate sizing



import "celem.act";









// Baseline x1 uses default sizes
defcell C2x1 <: celem() {}</pre>

// Double size output inverter
defcell C2x2 <: celem() {sizing{out{-2}}}</pre>

// 2x logic stacks, 4x output inverter
defcell C2x4 <: celem()
{sizing{\_out{-2}; out{-4}}}</pre>

// That output inverter was a bit tall; fold in half
defcell C2x4F <: celem()
{sizing{\_out{-2}; out{-2,svt,2}}}</pre>

### Full custom flow example

